Hiroshi Yamaguchi

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/9000937/publications.pdf

Version: 2024-02-01

320	7,129	87888	82547
papers	citations	38 h-index	72 g-index

327	327	327	4895
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	On-Chip Coherent Transduction between Magnons and Acoustic Phonons in Cavity Magnomechanics. Physical Review Applied, 2022, 17, .	3.8	24
2	Development of an Optomechanical Device with Extremely Low Optical Energy Loss. NTT Technical Review, 2022, 20, 49-53.	0.1	0
3	Fabrication of Suspended Nanowire Mechanical Devices Using Inkjet Technology. NTT Technical Review, 2022, 20, 59-64.	0.1	0
4	New Method of Chaos Generation by Using Nanomechanical Oscillator. NTT Technical Review, 2022, 20, 37-42.	0.1	0
5	Control of Elastic Waves Using Phonon Waveguides and Phononic Crystals. NTT Technical Review, 2022, 20, 43-48.	0.1	2
6	Double-Gate Vectorial Frequency Control in Piezoresistive Nanowire Electromechanical Devices. Physical Review Applied, 2022, 17, .	3.8	0
7	Buckling-induced quadratic nonlinearity in silicon phonon waveguide structures. Japanese Journal of Applied Physics, 2022, 61, SD1025.	1.5	3
8	Rare-Earth-Mediated Optomechanical System in the Reversed Dissipation Regime. Physical Review Letters, 2021, 126, 047404.	7.8	13
9	Generation and Propagation of Topological Solitons in a Chain of Coupled Parametric-Micromechanical-Resonator Arrays. Physical Review Applied, 2021, 15, .	3.8	4
10	Mode-sensitive magnetoelastic coupling in phononic-crystal magnomechanics. APL Materials, 2021, 9, 071110.	5.1	3
11	Non-equilibrium quadratic measurement-feedback squeezing in a micromechanical resonator. Physical Review Research, 2021, 3, .	3.6	1
12	Strain-mediated energy control of rare-earth ions toward a highly-coherent hybrid opto-mechanical system. , 2021, , .		0
13	Self-Sustained Libration Regime in Nonlinear Microelectromechanical Devices. Physical Review Applied, 2021, 16, .	3.8	3
14	Novel Fabrication Technique of Suspended Nanowire Devices for Nanomechanical Applications. Physica Status Solidi (B): Basic Research, 2020, 257, 1900401.	1.5	3
15	Generic Rotating-Frame-Based Approach to Chaos Generation in Nonlinear Micro- and Nanoelectromechanical System Resonators. Physical Review Letters, 2020, 125, 174301.	7.8	12
16	Mechanical Kerr Nonlinearity of Wave Propagation in an On-Chip Nanoelectromechanical Waveguide. Physical Review Applied, 2020, 13, .	3.8	15
17	Real-Space Characterization of Cavity-Coupled Waveguide Systems in Hypersonic Phononic Crystals. Physical Review Applied, 2020, 13, .	3.8	16
18	Demonstration of Multiple Internal Resonances in a Microelectromechanical Self-Sustained Oscillator. Physical Review Applied, 2020, 13, .	3.8	18

#	Article	IF	Citations
19	Near-field cavity optomechanical coupling in a compound semiconductor nanowire. Communications Physics, 2020, 3, .	5.3	4
20	Noise Reduction of a Mechanical Resonator by Laser Cooling. Vacuum and Surface Science, 2020, 63, 536-541.	0.1	0
21	Virtual Exceptional Points in an Electromechanical System. Physical Review Applied, 2019, 11, .	3.8	12
22	Pulse-width modulated oscillations in a nonlinear resonator under two-tone driving as a means for MEMS sensor readout. Japanese Journal of Applied Physics, 2019, 58, SBBI05.	1.5	4
23	Electron paramagnetic resonance spectroscopy using a single artificial atom. Communications Physics, 2019, 2, .	5.3	24
24	Strain-induced exciton decomposition and anisotropic lifetime modulation in a GaAs micromechanical resonator. Physical Review B, 2019, 99, .	3.2	0
25	Limit cycles and bifurcations in a nonlinear MEMS resonator with a 1:3 internal resonance. Applied Physics Letters, 2019, 114, .	3.3	34
26	Electrostatically Induced Phononic Crystal. Physical Review Applied, 2019, 11, .	3.8	26
27	On-Chip Piezoelectric Actuation of Nanomechanical Resonators Containing a Two-Dimensional Electron Gas. JETP Letters, 2019, 109, 261-265.	1.4	2
28	An AlGaAs/GaAs Mechanical Mode-Locked Cavity. , 2019, , .		0
29	Nonlinear Acoustic Dynamics in Nanoelectromechanical Waveguides. , 2019, , .		0
30	Novel Fabrication Technique of Suspended Nanowire Devices for Nanomechanical Applications. , 2019, , .		0
31	Modal Analysis Investigation of Mechanical Kerr Frequency Combs. Springer Proceedings in Physics, 2019, , 141-157.	0.2	1
32	ON-CHIP PIEZOELECTRIC ACTUATION OF NANOMECHANICAL RESONATORS CONTAINING A TWO-DIMENSIONAL ELECTRON GAS. Journal of Experimental and Theoretical Physics Letters, 2019, 109, 254-255.	0.1	0
33	On-chip temporal focusing of elastic waves in a phononic crystal waveguide. Nature Communications, 2018, 9, 1331.	12.8	46
34	Phonon-bottlenecked spin relaxation of Er³⁺:Y₂SiO₅at sub-kelvin temperatures. Applied Physics Express, 2018, 11, 043002.	2.4	12
35	Dynamical coupling between a nuclear spin ensemble and electromechanical phonons. Nature Communications, 2018, 9, 2993.	12.8	13
36	An opto-electro-mechanical system based on evanescently-coupled optical microbottle and electromechanical resonator. Applied Physics Letters, 2018, 112, .	3.3	13

#	Article	IF	Citations
37	Dynamic Control of the Coupling between Dark and Bright Excitons with Vibrational Strain. Physical Review Letters, 2018, 120, 267401.	7.8	16
38	Selective activation of localized mechanical resonators via a phonon waveguide. Applied Physics Letters, 2018, 113, 043104.	3.3	4
39	Electron paramagnetic resonance spectroscopy of Er3+:Y2SiO5 using a Josephson bifurcation amplifier: Observation of hyperfine and quadrupole structures. Physical Review Materials, 2018, 2, .	2.4	14
40	Feedback control of multiple mechanical modes in coupled micromechanical resonators. Applied Physics Letters, 2017, 110, 053106.	3.3	10
41	Broadband reconfigurable logic gates in phonon waveguides. Scientific Reports, 2017, 7, 12745.	3.3	15
42	GaAs-based micro/nanomechanical resonators. Semiconductor Science and Technology, 2017, 32, 103003.	2.0	47
43	A correlated electromechanical system. New Journal of Physics, 2017, 19, 033026.	2.9	3
44	Energy Dissipation in Graphene Mechanical Resonators with and without Free Edges. Micromachines, 2016, 7, 158.	2.9	14
45	Hopf and period-doubling bifurcations in an electromechanical resonator. Applied Physics Letters, 2016, 109, .	3.3	26
46	Enhanced visibility of two-mode thermal squeezed states via degenerate parametric amplification and resonance. New Journal of Physics, 2016, 18, 083009.	2.9	8
47	Electron paramagnetic resonance spectroscopy using a direct current-SQUID magnetometer directly coupled to an electron spin ensemble. Applied Physics Letters, 2016, 108, 052601.	3.3	21
48	A strongly coupled Î›-type micromechanical system. Applied Physics Letters, 2016, 108, .	3.3	23
49	Optically detected magnetic resonance of high-density ensemble of NV^{â^'}centers in diamond. Journal of Physics Condensed Matter, 2016, 28, 275302.	1.8	38
50	Multi-mode optical feedback control of GaAs mechanical resonators. , 2016, , .		0
51	An electromechanical Ising Hamiltonian. Science Advances, 2016, 2, e1600236.	10.3	73
52	Observation of Collective Coupling between an Engineered Ensemble of Macroscopic Artificial Atoms and a Superconducting Resonator. Physical Review Letters, 2016, 117, 210503.	7.8	62
53	Gate-controlled electromechanical backaction induced by a quantum dot. Nature Communications, 2016, 7, 11132.	12.8	47
54	A strict experimental test of macroscopic realism in a superconducting flux qubit. Nature Communications, 2016, 7, 13253.	12.8	105

#	Article	IF	Citations
55	Frequency division multiplexed logic circuits in a GaAs/AlGaAs-based phonon waveguide. , 2016, , .		0
56	Simulating the Ising Hamiltonian with phonons. , 2016, , .		0
57	An electromechanical displacement transducer. Applied Physics Express, 2016, 9, 086701.	2.4	2
58	Nanomechanical Resonators Based on IIIâ€“V Semiconductors. , 2016, , 1-17.		0
59	Nanomechanical Resonators Based on IIIâ€“V Semiconductors. , 2016, , 2523-2539.		1
60	Scalable quantum computation architecture using always-on Ising interactions via quantum feedforward. Physical Review A, 2015, 91, .	2.5	2
61	Proposed Robust Entanglement-Based Magnetic Field Sensor Beyond the Standard Quantum Limit. Physical Review Letters, 2015, 115, 170801.	7.8	44
62	Optically induced strong intermodal coupling in mechanical resonators at room temperature. Applied Physics Letters, 2015, 107, .	3.3	7
63	Phonon propagation dynamics in band-engineered one-dimensional phononic crystal waveguides. New Journal of Physics, 2015, 17, 113032.	2.9	17
64	Dispersive and Dissipative Coupling in a Micromechanical Resonator Embedded with a Nanomechanical Resonator. Nano Letters, 2015, 15, 2312-2317.	9.1	43
65	Renovation of three-dimensional electron beam lithography for improvement of positioning accuracy and reduction of turnaround time. Japanese Journal of Applied Physics, 2015, 54, 06FD02.	1.5	2
66	Improving the lifetime of the nitrogen-vacancy-center ensemble coupled with a superconducting flux qubit by applying magnetic fields. Physical Review A, 2015, 91, .	2.5	24
67	Improving the Coherence Time of a Quantum System via a Coupling to a Short-Lived System. Physical Review Letters, 2015, 114, 120501.	7.8	23
68	Analysis of the spectroscopy of a hybrid system composed of a superconducting flux qubit and diamond NVâ^'centers. Journal of Physics Condensed Matter, 2015, 27, 345702.	1.8	2
69	Observing the semiconducting band-gap alignment of MoS2 layers of different atomic thicknesses using a MoS2/SiO2/Si heterojunction tunnel diode. Applied Physics Letters, 2015, 107, .	3.3	8
70	Cavity-less on-chip optomechanics using excitonic transitions in semiconductor heterostructures. Nature Communications, 2015, 6, 8478.	12.8	24
71	Hybridization: When two wrongs make a right. , 2015, , .		0
72	Mechanical random access memory in a phonon circuit. Applied Physics Express, 2014, 7, 125201.	2.4	15

#	Article	IF	Citations
73	Rapid switching in high-Q mechanical resonators. Applied Physics Letters, 2014, 105, .	3.3	22
74	Nonlinear optical spectra having characteristics of Fano interferences in coherently coupled lowest exciton biexciton states in semiconductor quantum dots. AIP Advances, 2014, 4, 107124.	1.3	0
75	Entangled-state generation and Bell inequality violations in nanomechanical resonators. Physical Review B, 2014, 90, .	3.2	32
76	Two-Mode Thermal-Noise Squeezing in an Electromechanical Resonator. Physical Review Letters, 2014, 113, 167203.	7.8	67
77	Energy dissipation in edged and edgeless graphene mechanical resonators. Journal of Applied Physics, 2014, 116, 064304.	2.5	13
78	Nonlinear dynamics and all mechanical phonon lasing in electromechanical resonators. , 2014, , .		1
79	Mechanical resonance characteristics of a cylindrical semiconductor heterostructure containing a high-mobility two-dimensional electron gas. Physical Review B, 2014, 89, .	3.2	1
80	Stability and Reactivity of [11-20] Step in Initial Stage of Epitaxial Graphene Growth on SiC(0001). Materials Science Forum, 2014, 778-780, 1150-1153.	0.3	0
81	Fabrication of Electrostatically Actuated 4H-SiC Microcantilever Resonators by Using n/p/n Epitaxial Structures and Doping-Selective Electrochemical Etching. Materials Science Forum, 2014, 778-780, 780-783.	0.3	2
82	Direct fabrication of a W-C SNS Josephson junction using focused-ion-beam chemical vapour deposition. Journal of Micromechanics and Microengineering, 2014, 24, 055015.	2.6	6
83	Phonon waveguides for electromechanical circuits. Nature Nanotechnology, 2014, 9, 520-524.	31.5	118
84	Theoretical studies of graphene on SiC. , 2014, , .		0
85	Nonlinear electromechanical resonators ~ from phonon lasing operation to nanomechanical processors. , 2014, , .		1
86	A multimode electromechanical parametric resonator array. Scientific Reports, 2014, 4, 4448.	3.3	62
87	Coherent phonon manipulation in coupled mechanical resonators. Nature Physics, 2013, 9, 480-484.	16.7	274
88	Graphene-Based Nano-Electro-Mechanical Switch with High On/Off Ratio. Applied Physics Express, 2013, 6, 055101.	2.4	28
89	Single-crystalline 4H-SiC micro cantilevers with a high quality factor. Sensors and Actuators A: Physical, 2013, 197, 122-125.	4.1	20
90	Phonon Lasing in an Electromechanical Resonator. Physical Review Letters, 2013, 110, 127202.	7.8	127

#	Article	IF	Citations
91	Ferromagnetic-induced component in piezoresistance of GaMnAs. Physical Review B, 2013, 87, .	3.2	9
92	Self-sustained oscillations of a torsional SQUID resonator induced by Lorentz-force back-action. Nature Communications, 2013, 4, 1803.	12.8	17
93	A phonon transistor in an electromechanical resonator array. Applied Physics Letters, 2013, 102, .	3.3	31
94	Superconductivity in Tungsten-Carbide Nanowires Deposited from the Mixtures of W(CO)₆and C₁₄H₁₀. Japanese Journal of Applied Physics, 2013, 52, 075001.	1.5	12
95	Universal three-dimensional nanofabrication for hard materials. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 051802.	1.2	1
96	Role of step in initial stage of graphene growth on SiC(0001). , 2013, , .		0
97	Parametric mode mixing in asymmetric doubly clamped beam resonators. New Journal of Physics, 2013, 15, 015023.	2.9	22
98	Ultrahigh-QMicromechanical Resonators by Using Epitaxially Induced Tensile Strain in GaNAs. Applied Physics Express, 2013, 6, 111201.	2.4	15
99	Epitaxial Trilayer Graphene Mechanical Resonators Obtained by Electrochemical Etching Combined with Hydrogen Intercalation. Japanese Journal of Applied Physics, 2013, 52, 04CH01.	1.5	13
100	Direct Biexciton Creation with Two-Photon Excitation for Ideal Entangled Photon Pair Emissions in Optically Active Quantum Dots. Japanese Journal of Applied Physics, 2013, 52, 120202.	1.5	2
101	Modifying exciton optical properties in quantum dots with coherent phonons induced by ultrafast optical pulses. Applied Physics Letters, 2013, 103, 112104.	3.3	3
102	Multi-mode parametric coupling in an electromechanical resonator. Applied Physics Letters, 2013, 103, .	3.3	32
103	Quantum point contact displacement transducer for a mechanical resonator at sub-Kelvin temperatures. Applied Physics Letters, 2013, 103, 192105.	3.3	24
104	Wide-bandwidth charge sensitivity with a radio-frequency field-effect transistor. Applied Physics Letters, 2013, 103, 143102.	3.3	9
105	Stability and reactivity of steps in the initial stage of graphene growth on the SiC(0001) surface. Physical Review B, 2013, 88, .	3.2	16
106	Fano Quantum Interference Effects in Exciton-Biexciton Coherently Coupled System in Quantum Dots. , 2013, , .		0
107	Electron beam lithography on vertical side faces of micrometer-order Si block. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 041601.	1.2	7
108	An electromechanical membrane resonator. Applied Physics Letters, 2012, 101, 063102.	3.3	38

#	Article	IF	Citations
109	Spatially modulated photoluminescence properties in dynamically strained GaAs/AlAs quantum wells by surface acoustic wave. Applied Physics Letters, 2012, 100, .	3.3	7
110	Dynamic control of photoluminescence polarization properties in GaAs/AlAs quantum wells by surface acoustic waves. Physical Review B, 2012, 86, .	3.2	2
111	Tuneable electromechanical comb generation. Applied Physics Letters, 2012, 100, .	3.3	17
112	Motion detection of a micromechanical cantilever through magneto-piezovoltage in two-dimensional electron systems. Applied Physics Letters, 2012, 100, 012106.	3.3	8
113	Optomechanical photoabsorption spectroscopy of exciton states in GaAs. Applied Physics Letters, 2012, 101, 082107.	3.3	10
114	Charged exciton creation with two-color optical excitation method and analysis of initialization process of electron spin qubit in quantum dots. Journal of Applied Physics, 2012, 111, 123520.	2.5	2
115	Coherent Control of Micro/Nanomechanical Oscillation Using Parametric Mode Mixing. Applied Physics Express, 2012, 5, 014001.	2.4	21
116	Microscopic Raman Mapping of Epitaxial Graphene on 4H-SiC(0001). Japanese Journal of Applied Physics, 2012, 51, 06FD06.	1.5	3
117	Mechanical vibration of a cylindrically rolled-up cantilever shell in microelectromechanical and nanoelectromechanical systems. Physical Review B, 2012, 85, .	3.2	4
118	Electrical characteristics of inâ€plane gate logic devices. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 385-388.	0.8	1
119	Phonon-cavity electromechanics. Nature Physics, 2012, 8, 387-392.	16.7	127
120	Microscopic Raman Mapping of Epitaxial Graphene on 4H-SiC(0001). Japanese Journal of Applied Physics, 2012, 51, 06FD06.	1.5	5
121	Wide-band idler generation in a GaAs electromechanical resonator. Physical Review B, 2011, 84, .	3.2	22
122	dc SQUIDs as linear displacement detectors for embedded micromechanical resonators. Comptes Rendus Physique, 2011, 12, 817-825.	0.9	3
123	Discrete-time quadrature feedback cooling of a radio-frequency mechanical resonator. Applied Physics Letters, 2011, 99, .	3.3	14
124	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. Japanese Journal of Applied Physics, 2011, 50, 070115.	1.5	8
125	Atomic Structure of Epitaxial Graphene Islands on SiC(0001) Surfaces and their Magnetoelectric Effects. , 2011, , .		0
126	Theoretical Study on Epitaxial Graphene Growth by Si Sublimation from SiC(0001) Surface. Japanese Journal of Applied Physics, 2011, 50, 095601.	1.5	8

#	Article	IF	Citations
127	Operating principle and integration of in-plane gate logic devices. Applied Physics Letters, 2011, 99, 242106.	3.3	7
128	Carrier-mediated optomechanical coupling in GaAs cantilevers. Physical Review B, 2011, 84, .	3.2	7
129	Creation of charged excitons with two-color excitation method and initialization of electron spin qubit in quantum dots. Applied Physics Letters, 2011, 98, .	3.3	4
130	High-sensitivity charge detection using antisymmetric vibration in coupled micromechanical oscillators. Applied Physics Letters, 2011, 98, .	3.3	33
131	Vibration Amplification, Damping, and Self-Oscillations in Micromechanical Resonators Induced by Optomechanical Coupling through Carrier Excitation. Physical Review Letters, 2011, 106, 036801.	7.8	51
132	Electromechanical Displacement Detection With an On-Chip High Electron Mobility Transistor Amplifier. Japanese Journal of Applied Physics, 2011, 50, 06GJ01.	1.5	1
133	Interconnect-free parallel logic circuits in a single mechanical resonator. Nature Communications, 2011, 2, 198.	12.8	140
134	Remote actuation of a mechanical resonator. Applied Physics Letters, 2011, 99, 103105.	3.3	1
135	Electromechanical Displacement Detection With an On-Chip High Electron Mobility Transistor Amplifier. Japanese Journal of Applied Physics, 2011, 50, 06GJ01.	1.5	3
136	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. Japanese Journal of Applied Physics, 2011, 50, 070115.	1.5	9
137	Theoretical Study on Epitaxial Graphene Growth by Si Sublimation from SiC(0001) Surface. Japanese Journal of Applied Physics, 2011, 50, 095601.	1.5	9
138	Feedback Cooling of a Strained GaAs Micromechanical Beam Resonator. Applied Physics Express, 2010, 3, 065201.	2.4	6
139	Time-Resolved Kerr Rotation Spectroscopy of Spin Dynamics in a Quantum Hall System. , 2010, , .		0
140	Contact Conductance Measurement of Locally Suspended Graphene on SiC. Applied Physics Express, 2010, 3, 045101.	2.4	20
141	Tunable coupling of mechanical vibration in GaAs micro-resonators. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2849-2852.	2.7	6
142	Atomic Structure and Physical Properties of Epitaxial Graphene Islands Embedded in SiC(0001) Surfaces. Applied Physics Express, 2010, 3, 115103.	2.4	10
143	A symmetry-breaking electromechanical detector. Applied Physics Letters, 2010, 96, .	3.3	15
144	Tunable Backaction of a DC SQUID on an Integrated Micromechanical Resonator. Physical Review Letters, 2010, 105, 207203.	7.8	28

#	Article	IF	Citations
145	Enhanced force sensitivity and noise squeezing in an electromechanical resonator coupled to a nanotransistor. Applied Physics Letters, 2010, 97, 253105.	3.3	18
146	Resist Coating on Vertical Side Faces Using Conventional Spin Coating for Creating Three-Dimensional Nanostructures in Semiconductors. Applied Physics Express, 2010, 3, 106501.	2.4	8
147	Controlling Quality Factor in Micromechanical Resonators by Carrier Excitation. Applied Physics Express, 2009, 2, 035001.	2.4	7
148	Magneto-optical spectroscopy of excitons and trions in charge-tunable quantum dots. Physical Review B, 2009, 79, .	3.2	11
149	Room temperature piezoelectric displacement detection via a silicon field effect transistor. Applied Physics Letters, 2009, 95, .	3.3	15
150	Photoluminescence dynamics in GaAs/AlAs quantum wells modulated by one-dimensional standing surface acoustic waves. Applied Physics Letters, 2009, 94, .	3.3	6
151	Local conductance measurements of double-layer graphene on SiC substrate. Nanotechnology, 2009, 20, 445704.	2.6	38
152	ELECTRON SPIN IMAGING IN QUANTUM HALL DEVICES BY KERR ROTATION MEASUREMENT. International Journal of Modern Physics B, 2009, 23, 2750-2754.	2.0	0
153	OPTICALLY INDUCED DYNAMIC NUCLEAR SPIN POLARIZATION IN QUANTUM HALL REGIME OBSERVED BY A TIME-RESOLVED KERR ROTATION. International Journal of Modern Physics B, 2009, 23, 2755-2759.	2.0	1
154	Direct Actuation of GaAs Membrane with the Microprobe of Scanning Probe Microscopy. Japanese Journal of Applied Physics, 2009, 48, 06FG06.	1.5	2
155	Evaluation of Thermalâ€“Mechanical Vibration Amplitude and Mechanical Properties of Carbon Nanopillars Using Scanning Electron Microscopy. Japanese Journal of Applied Physics, 2009, 48, 06FG07.	1.5	4
156	Focus on Novel Nanoelectromechanical 3D Structures: Fabrication and Properties. Science and Technology of Advanced Materials, 2009, 10, 030301.	6.1	0
157	Stacking domains of epitaxial few-layer graphene on SiC(0001). Physical Review B, 2009, 80, .	3.2	84
158	Spatial and temporal modulation of exciton photoluminescence properties in GaAs/AlAs dynamic quantum dots formed by surface acoustic waves. Physical Review B, 2009, 80, .	3.2	10
159	MICRO/NANOMECHANICAL SYSTEMS FOR INFORMATION PROCESSING. , 2009, , .		0
160	Spin selective optical excitation in chargeâ€tunable GaAs quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2904-2906.	0.8	1
161	Mechanically detected field-induced Mn spin rotation in GaMnAs. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2893-2895.	0.8	0
162	Twoâ€Dimensional Patterning of Flexible Designs with High Halfâ€Pitch Resolution by Using Block Copolymer Lithography. Advanced Materials, 2008, 20, 1684-1689.	21.0	29

#	Article	IF	Citations
163	Magnetic field induced by the carbon nanotubes current by magnetic force microscopy. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2220-2221.	2.7	4
164	Bit storage and bit flip operations in an electromechanical oscillator. Nature Nanotechnology, 2008, 3, 275-279.	31.5	269
165	Motion detection of a micromechanical resonator embedded in a d.c. SQUID. Nature Physics, 2008, 4, 785-788.	16.7	166
166	Three-dimensional alignment with 10nm order accuracy in electron-beam lithography on rotated sample for three-dimensional nanofabrication. Journal of Vacuum Science & Technology B, 2008, 26, 2529-2533.	1.3	13
167	Thermoelastic damping in GaAs micromechanical resonators. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2920-2922.	0.8	12
168	In-plane conductance measurement of graphene nanoislands using an integrated nanogap probe. Nanotechnology, 2008, 19, 495701.	2.6	22
169	Microscopic thickness determination of thin graphite films formed on<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>SiC</mml:mi></mml:mrow></mml:math>from quantized oscillation in reflectivity of low-energy electrons. Physical Review B, 2008, 77, .	3.2	330
170	Single-Electron-Resolution Electrometer Based on Field-Effect Transistor. Japanese Journal of Applied Physics, 2008, 47, 8305-8310.	1.5	30
171	Cooling of a micro-mechanical resonator by the back-action of Lorentz force. New Journal of Physics, 2008, 10, 043015.	2.9	28
172	Height Dependence of Young's Modulus for Carbon Nanopillars Grown by Focused-Ion-Beam-Induced Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2008, 47, 5116-5119.	1.5	7
173	Low-Energy Electron Emission from an Electron Enversion Layer of a Si/SiO2/Si Cathode for Nano-Decomposition. Japanese Journal of Applied Physics, 2008, 47, 5106-5108.	1.5	1
174	Parametrically pumped ultrahigh Q electromechanical resonator. Applied Physics Letters, 2008, 92, 253109.	3.3	25
175	Piezoelectrically pumped parametric amplification and Q enhancement in an electromechanical oscillator. Applied Physics Letters, 2008, 92, 173109.	3.3	44
176	Improved resonance characteristics of GaAs beam resonators by epitaxially induced strain. Applied Physics Letters, 2008, 92, 251913.	3.3	35
177	On-chip Micromechanical Parametric Resonator Based on the Piezoelectricity in GaAs/AlGaAs Modulation-Doped Heterostructure. , 2008, , .		0
178	Electron-Spin Manipulation and Resonator Readout in a Double-Quantum-Dot Nanoelectromechanical System. Physical Review Letters, 2008, 100, 136802.	7.8	21
179	Spin dynamics of two-dimensional electrons in a quantum Hall system probed by time-resolved Kerr rotation spectroscopy. Physical Review B, 2008, 78, .	3.2	28
180	Local conductance measurement of few-layer graphene on SiC substrate using an integrated nanogap probe. Journal of Physics: Conference Series, 2008, 100, 052006.	0.4	8

#	Article	IF	Citations
181	Thickness Determination of Graphene Layers Formed on SiC Using Low-Energy Electron Microscopy. E-Journal of Surface Science and Nanotechnology, 2008, 6, 107-110.	0.4	46
182	Field-Effect Transistor with Deposited Graphite Thin Film. Japanese Journal of Applied Physics, 2007, 46, 2615-2617.	1.5	4
183	Two-dimensional Arrangement of Vertically Oriented Cylindrical Domains of Diblock Copolymers using Graphoepitaxy with Artificial Guiding Pattern Layout. , 2007, , .		0
184	Controllable coupling between flux qubit and nanomechanical resonator by magnetic field. New Journal of Physics, 2007, 9, 35-35.	2.9	75
185	Giant Magneto-Piezoresistance and Internal Friction in a Two-Dimensional Electron System. Japanese Journal of Applied Physics, 2007, 46, L658-L660.	1.5	7
186	Modulation of Young's Modulus of Poly(methyl methacrylate) Nanobeam Due to Electron-Beam Exposure. Japanese Journal of Applied Physics, 2007, 46, L1225-L1227.	1.5	7
187	Local Conductance Imaging of Semiconductor Nanowires on an Insulative Substrate Using an Integrated Nanogap Probe. Japanese Journal of Applied Physics, 2007, 46, 5639.	1.5	4
188	Infrared detection with silicon nano-field-effect transistors. Applied Physics Letters, 2007, 90, 223108.	3.3	17
189	Conductance modulation by individual acceptors in Si nanoscale field-effect transistors. Applied Physics Letters, 2007, 90, 102106.	3.3	90
190	Impact of Space-Energy Correlation on Variable Range Hopping in a Transistor. Physical Review Letters, 2007, 98, 166601.	7.8	4
191	Control of Young's Modulus for Carbon Nanopillars Grown by Focused Ion Beam Induced Chemical Vapor Deposition. , 2007, , .		0
192	Growth of very-high-mobility AlGaSbâˆ•InAs high-electron-mobility transistor structure on si substrate for high speed electronic applications. Applied Physics Letters, 2007, 90, 023509.	3.3	20
193	Photoluminescence Dynamics of GaAs/AlAs Quantum Wells Modulated by Surface Acoustic Waves. Japanese Journal of Applied Physics, 2007, 46, L758-L760.	1.5	8
194	Pattern Transfer of Laterally Aligned Lamellar Domains of Diblock Copolymers. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2007, 20, 767-769.	0.3	2
195	Nanogap electrodes on Si cantilever for local conductance measurement. Journal of Physics: Conference Series, 2007, 61, 856-860.	0.4	10
196	Electron phase modulation in a high Q nanomechanical resonator. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	0
197	Mechanically detected electron energy dissipation in two-dimensional electron systems. AIP Conference Proceedings, 2007, , .	0.4	0
198	Piezoresistance of suspended InAs/AlGaSb heterostructure nanobeam. Journal of Crystal Growth, 2007, 301-302, 897-901.	1.5	2

#	Article	IF	Citations
199	Magnetization of free standing GaMnAs. Journal of Crystal Growth, 2007, 308, 204-207.	1.5	1
200	Semiconductor heterostructure studies using emerging technologies. Physica Status Solidi (B): Basic Research, 2007, 244, 2988-3001.	1.5	5
201	A $delta$-Doped InGaP/InGaAs pHEMT With Different Doping Profiles for Device-Linearity Improvement. IEEE Transactions on Electron Devices, 2007, 54, 1617-1625.	3.0	23
202	Transfer and Detection of Single Electrons Using Metal-Oxide-Semiconductor Field-Effect Transistors. IEICE Transactions on Electronics, 2007, E90-C, 943-948.	0.6	5
203	Device linearity comparison of uniformly doped and /spl delta/-doped In/sub 0.52/Al/sub 0.48/As/In/sub 0.6/Ga/sub 0.4/As metamorphic HEMTs. IEEE Electron Device Letters, 2006, 27, 535-537.	3.9	16
204	Corrections to â€œDevice Linearity Comparison of Uniformly Doped and$delta$-Doped$hboxIn_0.52hboxAl_0.48hboxAs/hboxIn_0.6hboxGa_0.4hboxAs$Metamorphic HEMTsâ€• IEEE Electron Device Letters, 2006, 27, 866-866.	3.9	0
205	Proposal of Carbon Nanotube Inductors. Journal of Physics: Conference Series, 2006, 38, 49-52.	0.4	13
206	Micromechanical Quantum Electron Transport. Journal of Physics: Conference Series, 2006, 38, 152-157.	0.4	1
207	Resist-Pattern Guided Self-assembly of Symmetric Diblock Copolymer. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2006, 19, 385-388.	0.3	14
208	Giant magnetopiezoresistance at the localized-extended electronic state transition in a high-mobility 2DEG system. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 663-666.	0.8	2
209	Enhanced emission of single quantum dot formed by interface fluctuations in photonic-crystal microcavities. Photonics and Nanostructures - Fundamentals and Applications, 2006, 4, 89-93.	2.0	0
210	A piezoresistive cantilever integrating an InAs-based semiconductorâ€“superconductor junction. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 512-515.	2.7	1
211	Carbon Multiprobe on a Si Cantilever for Pseudo-Metalâ€“Oxideâ€“Semiconductor Field-Effect-Transistor. Japanese Journal of Applied Physics, 2006, 45, 2009-2013.	1.5	8
212	Electron phase modulation in a suspended InAsâˆ•AlGaSb nanomechanical beam. Applied Physics Letters, 2006, 89, 192106.	3.3	7
213	Impurity conduction in phosphorus-doped buried-channel silicon-on-insulator field-effect transistors at temperatures between 10 and295K. Physical Review B, 2006, 74, .	3.2	15
214	Imaging of Local Tunneling Barrier Height of InAs Nanostructures Using Low-Temperature Scanning Tunneling Microscopy. AIP Conference Proceedings, 2005, , .	0.4	1
215	Difference in Self-Assembling Morphology of Peptide Nanorings. Japanese Journal of Applied Physics, 2005, 44, 8240-8248.	1.5	5
216	From ferro- to antiferromagnetism via exchange-striction of MnAs/GaAs(001). Europhysics Letters, 2005, 72, 479-485.	2.0	23

#	Article	IF	Citations
217	Strongly Enhanced Sensitivity of Piezoresistive Cantilevers by Utilizing the Superconducting Proximity Effect. Japanese Journal of Applied Physics, 2005, 44, L893-L895.	1.5	7
218	InAs-based Micromechanical Two-dimensional Electron Systems. AIP Conference Proceedings, 2005, , .	0.4	1
219	Force/displacement detection using quantum transport in InAsâˆ•AlGaSb two-dimensional heterostructures. Applied Physics Letters, 2005, 86, 052106.	3.3	16
220	Nonequilibrium transport of InAs/GaAs(111)A heterostructures coupled with superconducting Nb electrodes. Semiconductor Science and Technology, 2004, 19, S182-S184.	2.0	3
221	Quantum Interference Effects in the Magnetopiezoresistance ofInAs/AlGaSbQuasi-One-Dimensional Electron Systems. Physical Review Letters, 2004, 93, 036603.	7.8	16
222	InAs/AlGaSb Piezoresistive Cantilever for Sub-Angstrom Scale Displacement Detection. Japanese Journal of Applied Physics, 2004, 43, L424-L426.	1.5	3
223	Quantum-mechanical displacement sensing using InAs/AlGaSb micromechanical cantilevers. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 1053-1056.	2.7	5
224	InAs/GaAs (111)A heteroepitaxial systems. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 23, 285-292.	2.7	7
225	Piezoresistive cantilevers using InAs-based 2D Heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 24, 70-73.	2.7	2
226	Mechanical and piezoresistive properties of InAs/AlGaSb cantilevers. Applied Surface Science, 2004, 237, 645-649.	6.1	5
227	Perpendicular magnetic fields in cantilever beam magnetometry. Journal of Applied Physics, 2004, 96, 2773-2778.	2.5	8
228	Magnetoelastic coupling ofMnAsâˆ•GaAs(001)close to the phase transition. Physical Review B, 2004, 70, .	3.2	12
229	InAs/AlGaSb heterostructure displacement sensors for MEMS/NEMS applications. Journal of Crystal Growth, 2003, 251, 556-559.	1.5	8
230	Application of multi-step formation during molecular beam epitaxy for fabricating novel nanomechanical structures. Journal of Crystal Growth, 2003, 251, 281-284.	1.5	1
231	Fabrication and characterization of novel semiconductor nanomechanical structures. Surface Science, 2003, 532-535, 1171-1176.	1.9	2
232	Single-Turn GaAs/InAs Nanotubes Fabricated Using the Supercritical CO2Drying Technique. Japanese Journal of Applied Physics, 2003, 42, L791-L794.	1.5	37
233	Microelectromechanical displacement sensing using InAs/AlGaSb heterostructures. Applied Physics Letters, 2003, 82, 394-396.	3.3	28
234	Direct probing of local-density-of-states in semiconductor nanostructures. , 2003, , .		0

#	Article	IF	Citations
235	Fabrication of conductive single-crystal semiconductor nanoscale electromechanical structures. Applied Physics Letters, 2002, 80, 4428-4430.	3.3	14
236	Application of InAs Freestanding Membranes to Electromechanical Systems. Japanese Journal of Applied Physics, 2002, 41, 2519-2521.	1.5	4
237	Fabrication and elastic properties of InAs freestanding structures based on InAs/GaAs(111)A heteroepitaxial systems. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1163-1167.	2.7	7
238	First principles and macroscopic theories of semiconductor epitaxial growth. Journal of Crystal Growth, 2002, 237-239, 206-211.	1.5	14
239	Imaging of Zero-Dimensional States in Semiconductor Nanostructures Using Scanning Tunneling Microscopy. Lecture Notes in Physics, 2002, , 263-268.	0.7	0
240	Imaging of Friedel Oscillation Patterns of Two-Dimensionally Accumulated Electrons at Epitaxially Grown InAs(111)ASurfaces. Physical Review Letters, 2001, 86, 3384-3387.	7.8	122
241	Local Density of States in Zero-Dimensional Semiconductor Structures. Physical Review Letters, 2001, 87, 196804.	7.8	43
242	Excellent electric properties of free-standing InAs membranes. Applied Physics Letters, 2001, 78, 2372-2374.	3.3	27
243	Imaging of Friedel oscillations at epitaxially grown InAs(111) A surfaces using scanning tunneling microscopy. Springer Proceedings in Physics, 2001, , 427-430.	0.2	1
244	Electron and Hole Proximity Effects in the InAs/AlSb/GaSb System. Japanese Journal of Applied Physics, 2000, 39, 2448-2451.	1.5	8
245	Two-dimensional growth of InSb thin films on GaAs(111)A substrates. Applied Physics Letters, 2000, 76, 589-591.	3.3	61
246	Superconductor-semiconductor-superconductor junctions using NbN. Superconductor Science and Technology, 1999, 12, 901-903.	3.5	6
247	Drastic Improvement in Surface Flatness Properties by Using GaAs (111)A Substrates in Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1999, 38, 635-644.	1.5	18
248	SEM imaging of fundamental growth processes during MBE of GaAs on (111)A substrates. Journal of Crystal Growth, 1999, 201-202, 124-127.	1.5	2
249	First-principles calculations on atomic and electronic structures of misfit dislocations in InAs/GaAs(110) and GaAs/InAs(110) heteroepitaxies. Journal of Crystal Growth, 1999, 201-202, 256-259.	1.5	8
250	Vertical transport properties through pseudo-metallic InAs thin films grown on GaAs (111)A substrates. Journal of Crystal Growth, 1999, 201-202, 778-781.	1.5	3
251	Microscopic investigation of the surface phase transition on GaAs(001) surfaces. Surface Science, 1999, 433-435, 382-386.	1.9	11
252	First-principles calculation for misfit dislocations in InAs/GaAs(110) heteroepitaxy. Surface Science, 1999, 433-435, 900-903.	1.9	10

#	Article	IF	Citations
253	Imaging of Local Charge Density in an InAs/GaAs Two-Dimensional Heterostructure by Scanning Tunneling Microscopy. Japanese Journal of Applied Physics, 1998, 37, L899-L901.	1.5	7
254	Imaging of layer by layer growth processes during molecular beam epitaxy of GaAs on (111)A substrates by scanning electron microscopy. Applied Physics Letters, 1998, 73, 3079-3081.	3.3	22
255	Thickness-dependent electron accumulation in InAs thin films onGaAs(111)A:â€ƒA scanning-tunneling-spectroscopy study. Physical Review B, 1998, 58, R4219-R4222.	3.2	35
256	Improvement in the Electrical Properties of GaAs/InAs/GaAs Structures through the Use of (111)A Substrates. Japanese Journal of Applied Physics, 1998, 37, 1599-1602.	1.5	17
257	Scanning Tunneling Microscopy Study of GaAs (001) Surfaces Grown by Migration-Enhanced Epitaxy at Low Temperatures. Japanese Journal of Applied Physics, 1998, 37, 758-761.	1.5	5
258	Scanning tunneling microscopy studies of strain relaxation and misfit dislocations in InAs layers grown on GaAs(110) and GaAs(111)A. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1997, 15, 915-918.	2.1	21
259	Extremely long surface diffusion of Ga and critical nucleation on As-rich GaAs(001) surfaces caused by phase transitions. Physical Review B, 1997, 56, 12080-12083.	3.2	35
260	Atomic-scale imaging of strain relaxation via misfit dislocations in highly mismatched semiconductor heteroepitaxy: InAs/GaAs(111)A. Physical Review B, 1997, 55, 1337-1340.	3.2	136
261	A Scanning Tunneling Microscopy-Reflection High Energy Electron Diffraction-Rate Equation Study of the Molecular Beam Epitaxial Growth of InAs on GaAs(001), (110) and (111)Aâ€“Quantum Dots and Two-Dimensional Modes. Japanese Journal of Applied Physics, 1997, 36, 4111-4117.	1.5	83
262	RHEED and STM study of the two-dimensional growth of InAs on GaAs (111)A. Microelectronics Journal, 1997, 28, 825-831.	2.0	2
263	Precise control of two dimensional growth of InAs on GaAs (111)A surfaces studied by scanning tunneling microscopy. Applied Surface Science, 1997, 112, 138-141.	6.1	3
264	In situ observation of MEE GaAs growth using scanning electron microscopy. Journal of Crystal Growth, 1997, 175-176, 292-297.	1.5	5
265	Electronic properties of monolayer steps on GaAs (0 0 1) surfaces studied by scanning tunneling microscopy. Journal of Crystal Growth, 1997, 175-176, 304-309.	1.5	1
266	Structure analysis of the GaAs(001)-2 Ã— 4 surface using medium energy ion scattering. Surface Science, 1996, 355, L361-L365.	1.9	5
267	Reconstruction-dependent electron-hole recombination on GaAs(001) surfaces studied by using near-surface quantum wells. Physical Review B, 1996, 53, 7880-7883.	3.2	5
268	Electronic properties of monolayer steps on (2Ã—4)/c(2Ã—8) reconstructed GaAs(001) surfaces. Physical Review B, 1996, 54, 4428-4431.	3.2	11
269	Direct comparison of GaAs surface morphology between migration enhanced epitaxy and molecular beam epitaxy using in situ scanning electron microscopy. Applied Physics Letters, 1996, 68, 63-65.	3.3	27
270	Inhibitions of three dimensional island formation in InAs films grown on GaAs (111)A surface by molecular beam epitaxy. Applied Physics Letters, 1996, 69, 776-778.	3.3	121

#	Article	IF	Citations
271	Surface-defect formation on heavily doped InAs and GaAs layers studied by scanning tunneling microscopy. Physical Review B, 1996, 53, 4565-4569.	3.2	17
272	Direct determination of impact-parameter-dependent stopping powers for million-electron-volt He ions penetrating Er-doped GaAs. Physical Review A, 1996, 53, 1644-1652.	2.5	7
273	Effect of Growth Interruption during GaAs/AlGaAs Molecular Beam Epitaxy on (411)A Substrates. Japanese Journal of Applied Physics, 1996, 35, L822-L824.	1.5	3
274	Desorption and Segregation of Indium and its Dependence on Surface As-coverage. Materials Research Society Symposia Proceedings, 1995, 405, 31.	0.1	0
275	Unified model for first-order transition and electrical properties of InAs (001) surfaces based on atom-resolved scanning tunneling microscopy imaging. Journal of Crystal Growth, 1995, 150, 148-151.	1.5	4
276	Effects of alloy composition on the As desorption from and adsorption on strained InxGa1â^'xAs surfaces. Journal of Crystal Growth, 1995, 150, 473-477.	1.5	2
277	Structural analysis of erbium sheetâ€doped GaAs grown by molecularâ€beam epitaxy, with ion channeling followed by Monte Carlo simulation. Journal of Applied Physics, 1995, 77, 3095-3103.	2.5	12
278	Indium desorption from InAs surfaces and its dependence on As coverage. Applied Physics Letters, 1995, 67, 3948-3950.	3.3	5
279	In situ observation of phase transition and the transitionâ€induced step bunching on InAs(001) surfaces by scanning electron microscopy. Applied Physics Letters, 1995, 66, 1626-1628.	3.3	4
280	Flattening Transition on GaAs (411)A Surfaces Observed by Scanning Tunneling Microscopy. Japanese Journal of Applied Physics, 1995, 34, L1490-L1493.	1.5	17
281	Reconstruction Dependent Indium Segregation. Japanese Journal of Applied Physics, 1995, 34, L163-L166.	1.5	1
282	Surface structure transitions on InAs and GaAs (001) surfaces. Physical Review B, 1995, 51, 9836-9854.	3.2	98
283	Unified Model for Structure Transition and Electrical Properties of InAs (001) Surfaces Studied by Scanning Tunneling Microscopy. Japanese Journal of Applied Physics, 1994, 33, L1423-L1426.	1.5	35
284	Step Motion and Structure Transition on InAs and GaAs (001) Surfaces Observed by Scanning Tunneling Microscopy. Japanese Journal of Applied Physics, 1994, 33, 716-720.	1.5	15
285	Impact-parameter dependent stopping powers for axially channeled and semichanneled MeV He ions in GaAs:Er. Physical Review B, 1994, 49, 14387-14396.	3.2	14
286	Arsenic pressure dependence of firstâ€order phase transition on InAs (001) surface. Applied Physics Letters, 1994, 64, 2572-2574.	3.3	6
287	In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy. Applied Surface Science, 1994, 82-83, 223-227.	6.1	3
288	Phase transition on III-V compound semiconductor surfaces observed by an improved RHEED technique. Journal of Crystal Growth, 1993, 127, 976-980.	1.5	7

#	Article	IF	Citations
289	Observation of GaAs (001) surfaces at high temperatures by scanning tunneling microscopy. Journal of Crystal Growth, 1993, 127, 1064-1067.	1.5	3
290	Dependence of ErAs Clustering and Er Segregation in ErAs/GaAs Heterostructures on Growth Temperature. Japanese Journal of Applied Physics, 1993, 32, L1784-L1787.	1.5	15
291	Step motion and As desorption on InAs(001) surfaces observed by scanning tunneling microscopy. Physical Review B, 1993, 48, 2807-2810.	3.2	22
292	Scanning tunneling microscopy observation of monolayer steps on GaAs(001) vicinal surfaces grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1993, 63, 678-680.	3.3	23
293	Influence of monomolecular steps on the first-order structure transition of an InAs(001) surface. Physical Review Letters, 1993, 70, 1299-1302.	7.8	36
294	First-order surface-structure transition on the (001) InAs surface studied with improved high-energy electron reflectivity measurements. Physical Review B, 1992, 45, 1511-1513.	3.2	23
295	As desorption from GaAs and AlAs surfaces studied by improved highâ€energy electron reflectivity measurements. Journal of Applied Physics, 1992, 71, 1753-1759.	2.5	15
296	Growth of GaAs/ErAs/GaAs structures by migrationâ€enhanced epitaxy. Applied Physics Letters, 1992, 60, 2341-2343.	3.3	18
297	As desorption from GaAs and InAs surfaces studied by improved high-energy electron reflectivity measurements. Applied Surface Science, 1992, 60-61, 224-227.	6.1	4
298	Influence of surface reconstruction on the As desorption process from a (001) GaAs surface evaluated by improved high-energy electron-reflectivity measurements. Physical Review B, 1991, 44, 5897-5900.	3.2	17
299	Influence of an As-Free Atmosphere in Migration-Enhanced Epitaxy on Step-Flow Growth. Japanese Journal of Applied Physics, 1991, 30, 802-808.	1.5	20
300	Growth process of IIIâ€“V compound semiconductors by migration-enhanced epitaxy. Journal of Crystal Growth, 1990, 105, 326-338.	1.5	151
301	Replacement of groupâ€III atoms on the growing surface during migrationâ€enhanced epitaxy. Journal of Applied Physics, 1990, 68, 1610-1615.	2.5	60
302	Anomalous Distribution of In Atoms in GaAs during Migration-Enhanced Epitaxy. Japanese Journal of Applied Physics, 1989, 28, L2010-L2012.	1.5	10
303	Step-Flow Growth on Vicinal GaAs Surfaces by Migration-Enhanced Epitaxy. Japanese Journal of Applied Physics, 1989, 28, L1456-L1459.	1.5	44
304	Surface Migration of Ga and Al Atoms on (100) GaAs and AlAs during Migration-Enhanced Epitaxy. Japanese Journal of Applied Physics, 1989, 28, 1307-1311.	1.5	21
305	Luminescence Characteristics from Gaussian Shaped Quantum Wells. Japanese Journal of Applied Physics, 1989, 28, L507-L509.	1.5	3
306	Migration-enhanced epitaxy. Applied Surface Science, 1988, 33-34, 406-412.	6.1	9

#	Article	IF	Citations
307	Migration-Enhanced Epitaxy of GaAs and AlGaAs. Japanese Journal of Applied Physics, 1988, 27, 169-179.	1.5	353
308	Photoluminescence characteristics of AlGaAsâ€GaAs single quantum wells grown by migrationâ€enhanced epitaxy at 300â€‰Â°C substrate temperature. Applied Physics Letters, 1987, 50, 1686-1687.	3.3	49
309	N = 2 harmonic superspace with central charges and its application to self-interacting massive hypermultiplets. Annals of Physics, 1986, 172, 26-39.	2.8	11
310	Low-Temperature Growth of GaAs and AlAs-GaAs Quantum-Well Layers by Modified Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1986, 25, L868-L870.	1.5	369
311	Superfield perturbation theory in harmonic superspace. Physical Review D, 1985, 32, 1954-1967.	4.7	12
312	Dipole mechanism of spontaneous breaking ofN=2supersymmetry: Violation of positivity bound on central charges. Physical Review D, 1984, 30, 2181-2188.	4.7	3
313	Growth of atomically smooth ultra-thin InSb layers on GaAs substrates by molecular beam epitaxy. , 0, , .		0
314	Application of multistep formation during molecular beam epitaxy for fabricating novel nanomechanical structures. , 0, , .		0
315	Flexible Nanofabrication in Three-Dimensional Electron-Beam Lithography Enhanced by Suppression of Proximity Effect. Applied Physics Express, 0, 1, 097001.	2.4	10
316	Optical Tuning of Coupled Micromechanical Resonators. Applied Physics Express, 0, 2, 062202.	2.4	36
317	Theoretical Study of Epitaxial Graphene Growth on SiC(0001) Surfaces. Applied Physics Express, 0, 2, 065502.	2.4	62
318	High-Temperature Operation of Electrostatically-Excited Single-Crystalline 4H-SiC Microcantilever Resonators. Materials Science Forum, 0, 821-823, 914-918.	0.3	1
319	Fabrication of Nanomechanical Structures from Bulk-GaAs Using Angled Ion Etching. Applied Physics Express, 0, 2, 065001.	2.4	4
320	Quantum echoes. Nature Physics, 0, , .	16.7	0